

100mA 40V Low VF(0.37mm)

Chip Information

Chip Size	0.37 x 0.37mm
Pad Size	0.30 x 0.30mm
Chip Quantity	80698 pcs/wafer
Scribe Line Width	40um
Passivation	PSG
Wafer Size	5 inch
Top Metallization	Al(For Wire)

Chip Thickness/Back Metal : See below "Ordering Information"

MAXIMUM RATINGS

Parameter	Symbol	Limit	Unit	Note
Repetitive Peak Reverse Voltage	VRRM	45	V	
Non-Repetitive Peak Reverse Voltage	VRSM		V	
Maximum DC Blocking Voltage	VR	40	V	
Average Forward Rectified Current	IF(AV)	100	mA	
Peak Forward Surge Current	IFSM	1	A	8.3ms Single Half Sine-Wave
Storage and Operating Temperature Range	Tj,TSTG	-65 to +125	degC	

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Spec Limit	Probe Spec	Typical	Unit	Test Condition
Maximum Forward Voltage	VF1	0.550	0.520	0.450	V	IF=100mA Ta=25degC
	VF2	0.340	0.315	0.250	V	IF=10mA Ta=25degC
	VF3				V	
	VF4				V	
	VF5				V	
Maximum DC Reverse Current	IR1	30	10	2	uA	VR=10V Ta=25degC
	IR2				uA	
	IR3				uA	
	IR4				uA	
Reverse Breakdown Voltage	BV	45	47	60	V	IR=200uA
Junction Capacitance	Cj			5	pF	V=10V,f=1MHz
Reverse Recovery Time	trr				nS	

Ordering Information

Chip Type	Chip Thickness	Back Metal
YHM065	180 +/- 20um	Au(For Eutectic)
YHM067	150 +/- 20um	Au(For Eutectic)
YHM06Y	120 +/- 20um	Ti-Ni-Ag(For Ag Epoxy)

Note:

Designed For RB451F,RB425D,RB421D,RB501V-4